

Silicon PNP Power Transistors

2SB1149

DESCRIPTION

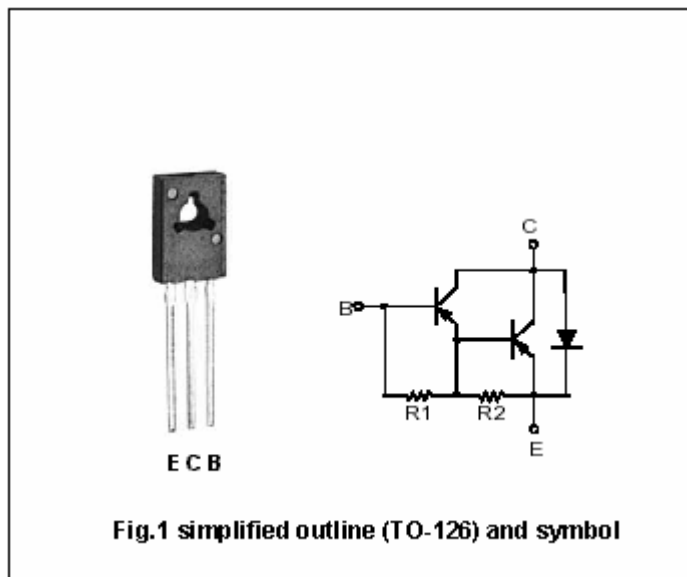
- With TO-126 package
- DARLINGTON
- High DC current gain
- Low collector saturation voltage

APPLICATIONS

- For use in operating from IC without predriver ,such as hammer driver

PINNING(See Fig.2)

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-8	V
I_C	Collector current (DC)		-3.0	A
I_{CM}	Collector current-peak		-5.0	A
P_D	Total power dissipation	$T_a=25^\circ\text{C}$	1.3	W
		$T_c=25^\circ\text{C}$	15	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-1.5A$; $I_B=-1.5mA$		-0.9	-1.2	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-1.5A$; $I_B=-1.5mA$		-1.5	-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-100V$; $I_E=0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V$; $I_C=0$			-2.0	mA
h_{FE-1}	DC current gain	$I_C=-1.5A$; $V_{CE}=-2V$	2000		15000	
h_{FE-2}	DC current gain	$I_C=-3A$; $V_{CE}=-2V$	1000			

Switching times

t_{on}	Turn-on time	$I_C=-1.5A$; $I_{B1}=-I_{B2}=-1.5mA$ $V_{CC}\approx -40V$; $R_L=27\Omega$		0.5		μs
t_{stg}	Storage time			2.0		μs
t_f	Fall time			1.0		μs

◆ h_{FE-1} Classifications

M	L	K
2000-5000	3000-7000	5000-15000

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PACKAGE OUTLINE

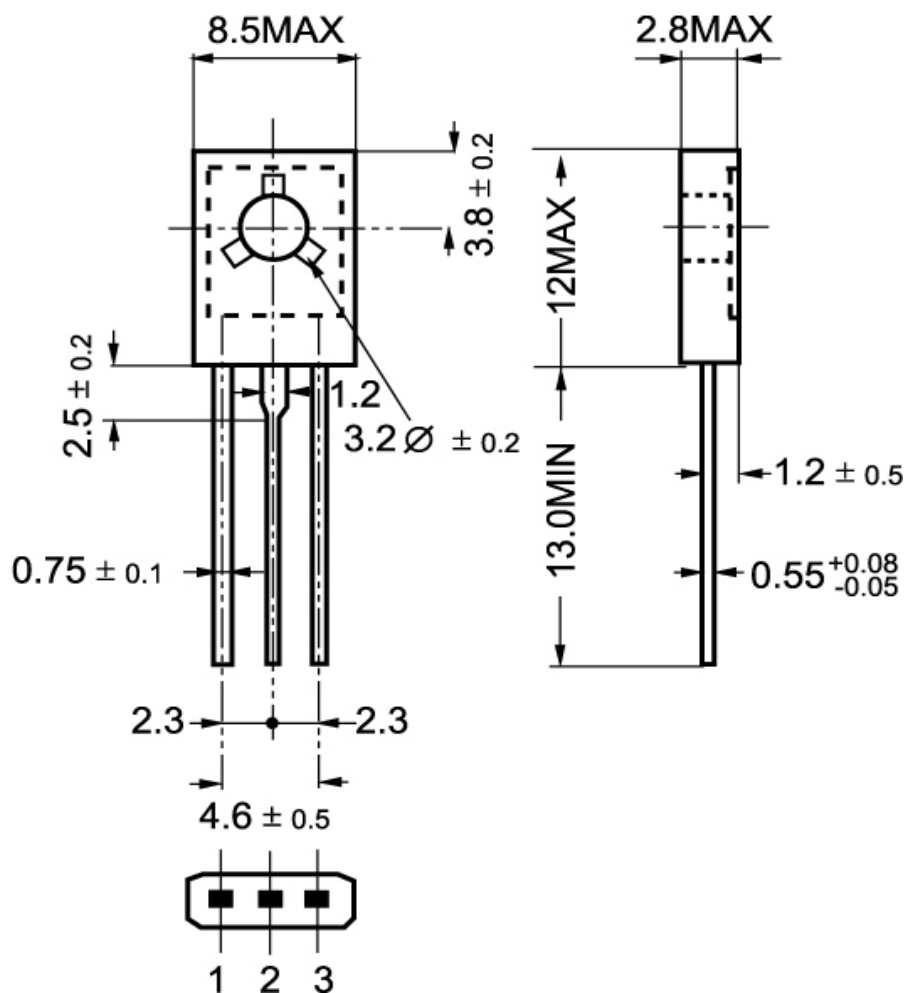


Fig.2 Outline dimensions